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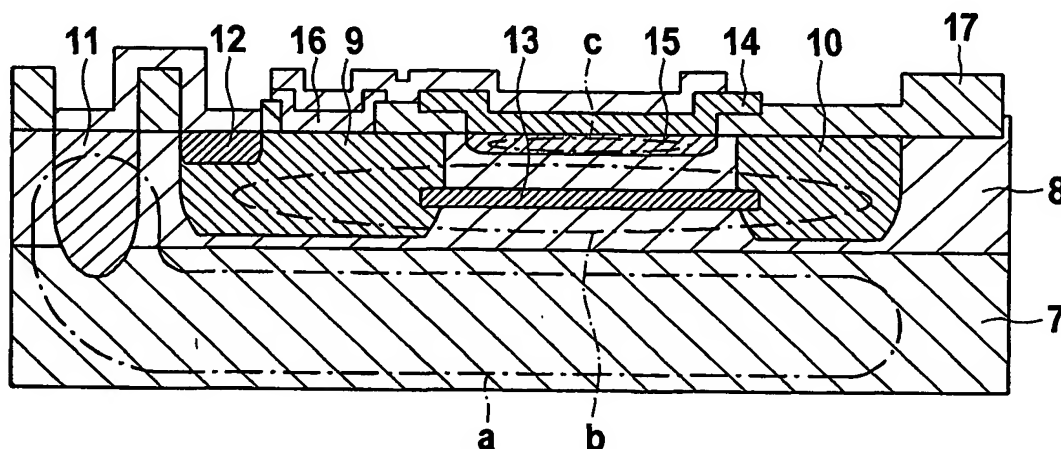
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(54) Title: PUNCH-THROUGH DIODE AND METHOD OF PROCESSING THE SAME



(57) Abstract: A monolithically integrated punch-through diode with a Schottky-like behavior. This is achieved as a Schottky-metal area (16) is deposited onto at least part of the first p-doped well's (9) surface. The Schottky-metal area (16) and the p-doped well (9) form the metal-semiconductor-transition of a Schottky-diode. The overvoltage protection of the inventive PT-diode is improved as the forward characteristic has a voltage drop that is less than 0.5V.

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